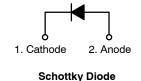
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Silicon Carbide (SiC) **Schottky Diode** – EliteSiC, 15 A, 1200 V, D1, TO-247-2L



FFSH15120A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 145 mJ

TO-247-2LD CASE 340CL MARKING DIAGRAM An and eling
An and eling
No Reverse Recovery/No Forward Recovery
This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant
Applications
General Purpose
SMPS, Solar Inverter, UPS
Power Switching Circuits
A YWW ZZ FFSH15120A AYWWZZ FFSH 15120A = Assembly Plant Code = Date Code (Year & Week) = Lot Code = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

| Symbol | Parameter | Value | Unit | |
|-----------------------------------|--|--|-------------|----|
| V _{RRM} | Peak Repetitive Reverse Voltage | 1200 | V | |
| E _{AS} | Single Pulse Avalanche Energy (Note 1) | 145 | mJ | |
| ١ _F | Continuous Rectified Forward Current @ $T_C < T_C$ | 15 | А | |
| | Continuous Rectified Forward Current @ T_C < | 26 | А | |
| I _{F,Max} | Non-Repetitive Peak Forward Surge Current | T _C = 25°C, 10 μs | 920 | А |
| | | T _C = 150°C, 10 μs | 870 | А |
| I _{F,SM} | Non-Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 115 | А |
| I _{F,RM} | Repetitive Forward Surge Current | Half–Sine Pulse, t _p = 8.3 ms | 50 | А |
| P _{TOT} | Power Dissipation | $T_{\rm C} = 25^{\circ}{\rm C}$ | 283 | W |
| | | T _C = 150°C | 47 | W |
| T _J , T _{STG} | Operating and Storage Temperature Range | • | -55 to +175 | °C |

ABSOLUTE MAXIMUM RATINGS (T_C = 25° C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| 1. E _{AS} of 145 m | sumed, damage may occur and J is based on starting T _J = 25° HARACTERISTICS | | = 50 V. | NDESI | _ | | |
|---|--|----------------|---------|-------|------|--|--|
| Symbol | | Parameter | | Value | Unit | | |
| $R_{	ext{	heta}JC}$ | Thermal Resistance, Junction | n to Case, Max | 10 CO | 0.53 | °C/W | | |
| ELECTRICAL CHARACTERISTICS (T _C = 25°C unless otherwise noted) | | | | | | | |
| Symbol | Parameter | Test Condition | Min Typ | Max | Unit | | |

| ELECTRICAL CHARACTERISTICS (T _C = 25°C unless otherwise noted) |
|---|
|---|

| Symbol | Parameter | Test Condition | Min | Тур | Max | Unit |
|----------------|-------------------------|---|----------------|------|------|------|
| V _F | Forward Voltage | I _F = 15 A, T _C = 25°C | 10 <u>-</u> 14 | 1.45 | 1.75 | V |
| | | I _F = 15 A, T _C = 125°C | <u>R-111</u> | 1.7 | 2.0 | |
| | | I _F = 15 A, T _C = 175°C | 0 | 2.0 | 2.4 | |
| I _R | Reverse Current | V _R = 1200 V, T _C = 25°C | - | - | 200 | μΑ |
| | SEISN. | V _R = 1200 V, T _C = 125°C | - | - | 300 | |
| | | V _R = 1200 V, T _C = 175°C | - | - | 400 | |
| Q _C | Total Capacitive Charge | V = 800 V | - | 95 | - | nC |
| С | Total Capacitance | V _R = 1 V, f = 100 kHz | - | 936 | - | pF |
| | SV SEY. | V _R = 400 V, f = 100 kHz | - | 86 | - |] |
| 1Y | | V _R = 800 V, f = 100 kHz | _ | 68 | - | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

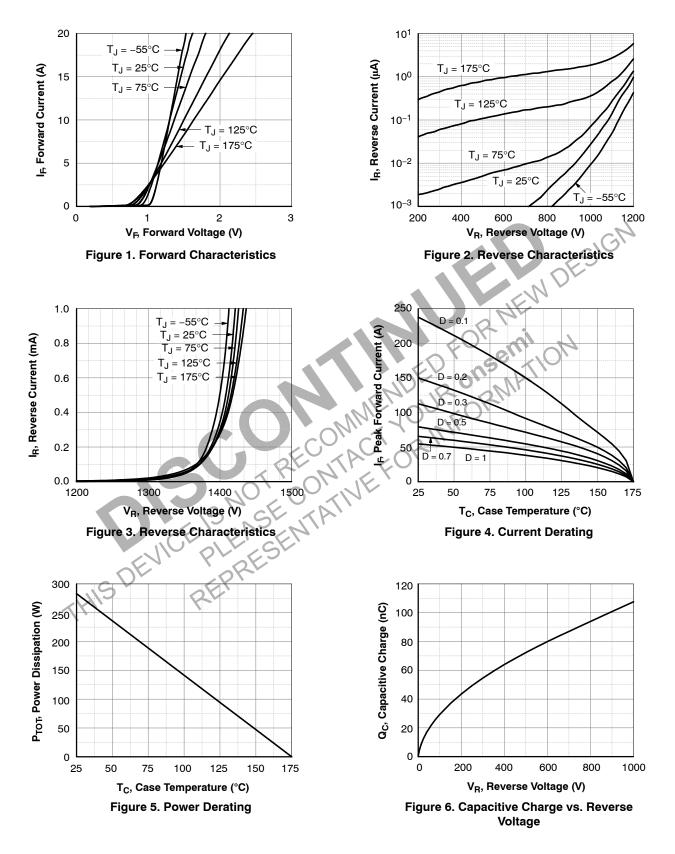
ORDERING INFORMATION

| Part Number | Top Marking | Package | Packing Method | Quantity |
|-------------|-------------|------------|----------------|----------|
| FFSH15120A | FFSH15120A | TO-247-2LD | Tube | 30 Units |

FFSH15120A

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)



FFSH15120A

 $\label{eq:typical characteristics} \begin{array}{l} \textbf{Typical characteristics} (\texttt{CONTINUED}) \\ (T_J = 25^\circ\texttt{C} \text{ UNLESS OTHERWISE NOTED}) \end{array}$

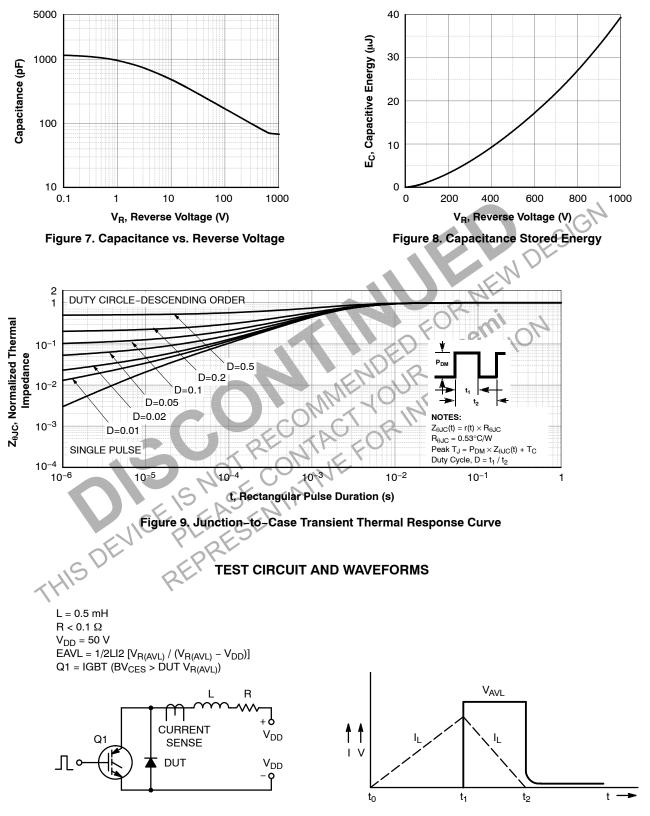


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

1

MILLIMETERS

NOM

4.70

2.40

1.50

1.26

1.65

0.61

20.57

16.57

0.93

15.62

~

5.08

11.12

16.00

3.81

3.58

6.73

5.46

5.46

MAX

4.82

2.66

1.70

1.35

1.77

0.71

20.82

16.77

1.35

15.87

~

5.20

~

16.25

3.93

3.65

6.85

5.58

5.58

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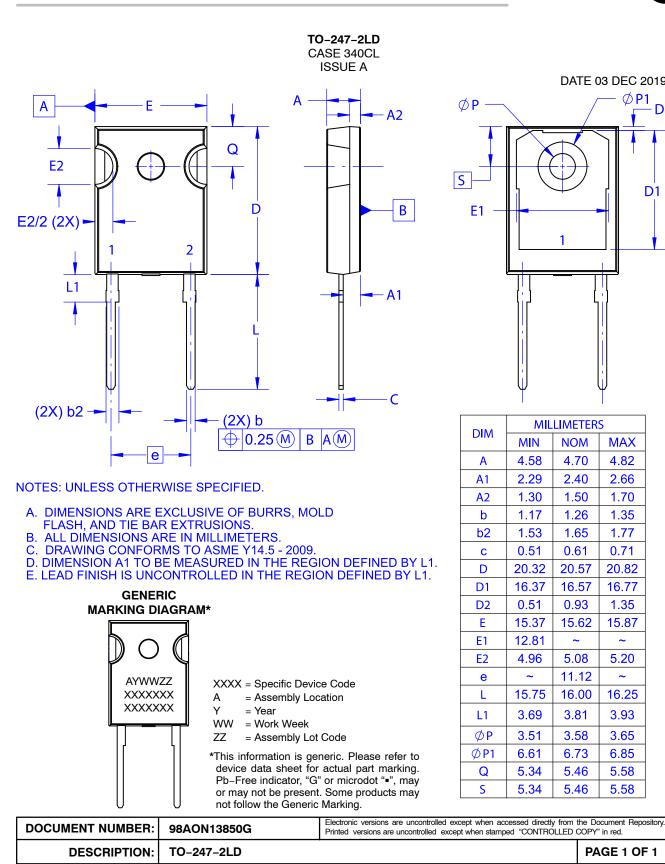
DATE 03 DEC 2019

ØP1



D2

D1



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